



SANYO Semiconductors

DATA SHEET

CPH6616 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.
- Excellent ON-resistance characteristic.
- Best suited for load switches.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		2.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	10	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² X0.8mm)1unit	0.9	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =1.5A	1.2	2.0		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =1.5A, V _{GS} =10V		79	105	mΩ
	R _{DS(on)2}	I _D =1A, V _{GS} =4V		150	210	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		187		pF
Output Capacitance	C _{oss}	V _{DS} =10V, f=1MHz		40		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =10V, f=1MHz		33		pF

Marking : WC

Continued on next page.

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CPH6616

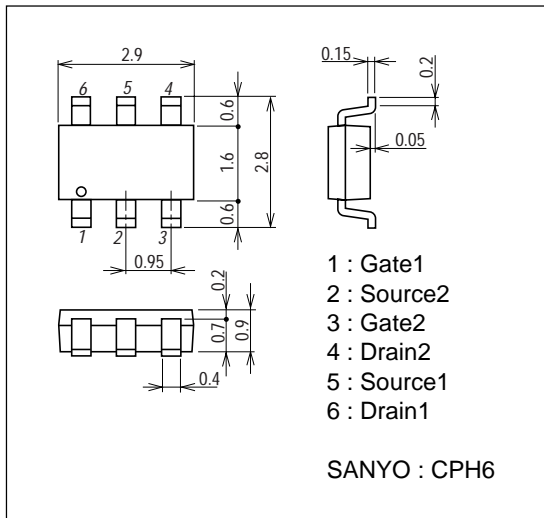
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		7.8		ns
Rise Time	t_r	See specified Test Circuit.		18.5		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		22		ns
Fall Time	t_f	See specified Test Circuit.		12		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		5.2		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		1		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=2.5A$		0.97		nC
Diode Forward Voltage	V_{SD}	$I_S=2.5A, V_{GS}=0$		0.9	1.2	V

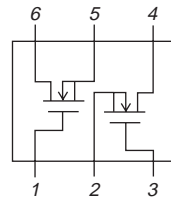
Package Dimensions

unit : mm

2238



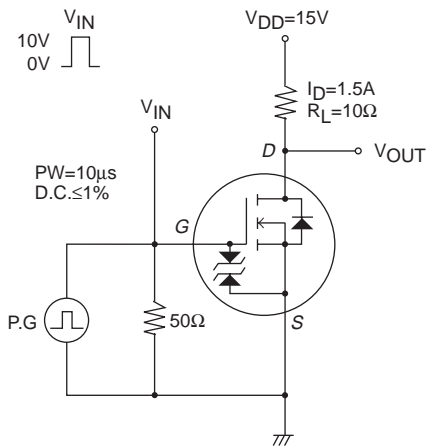
Electrical Connection

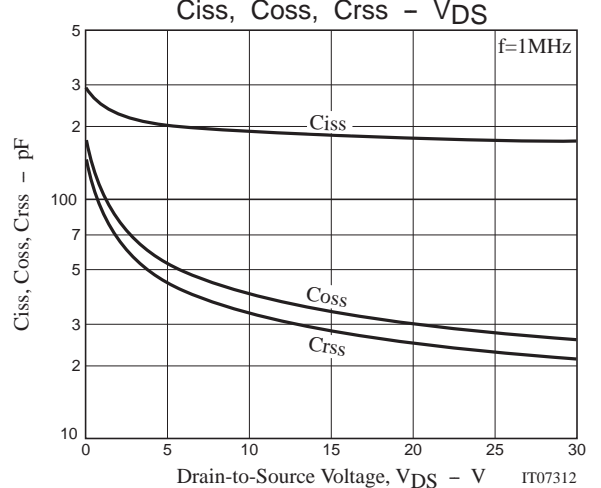
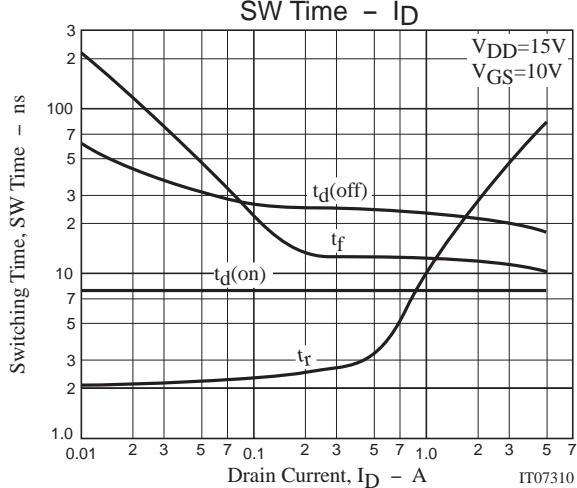
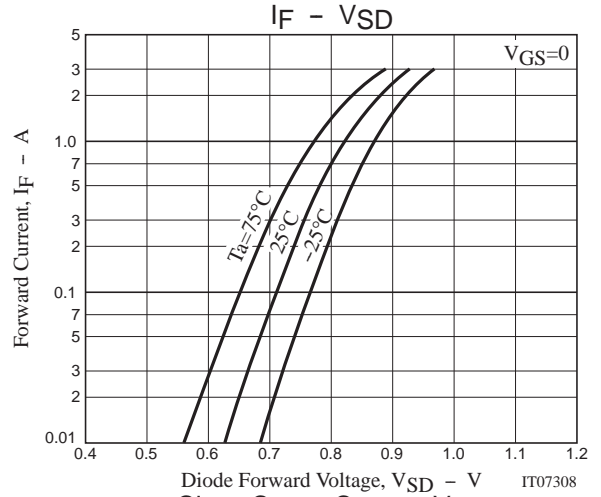
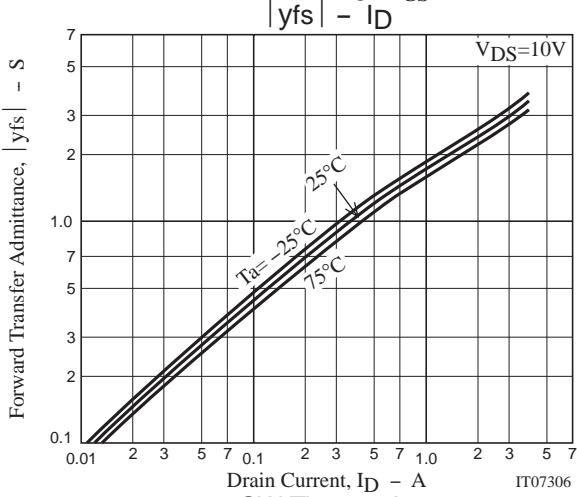
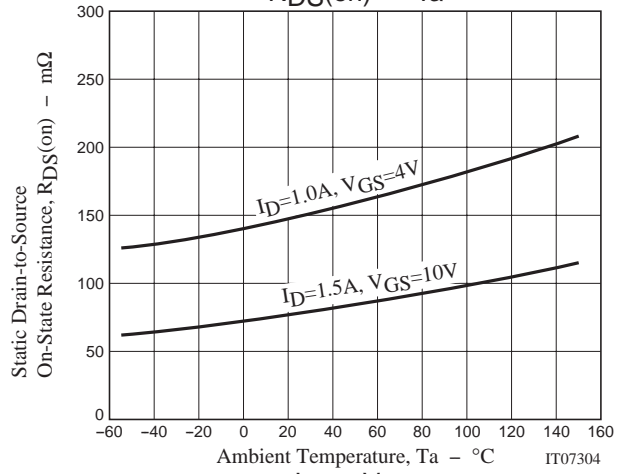
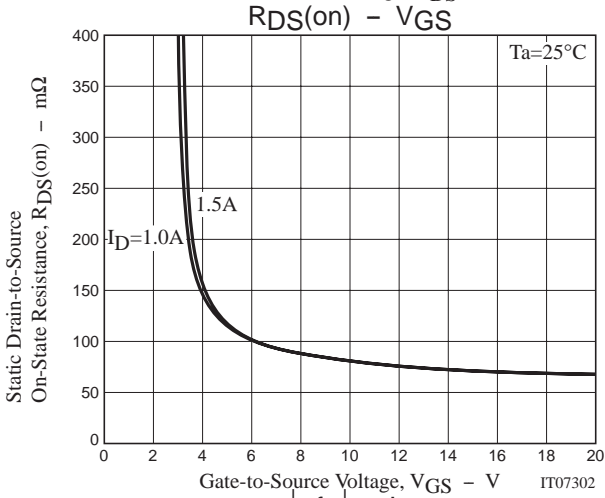
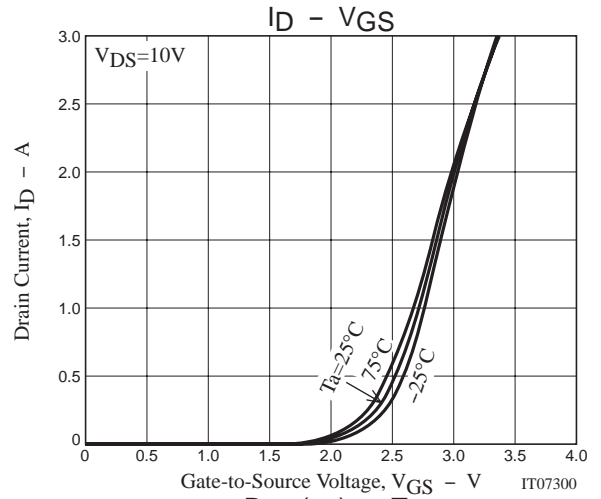
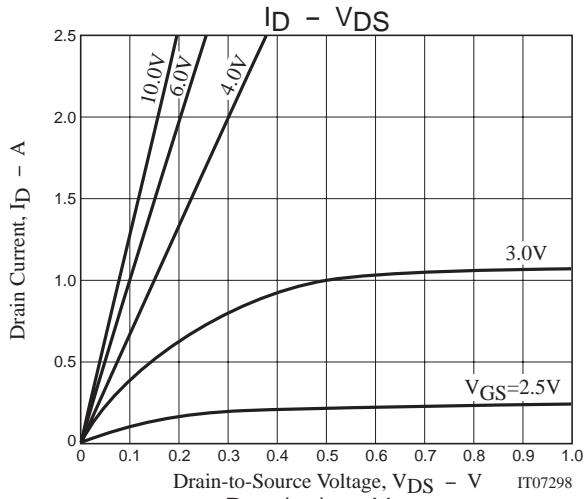


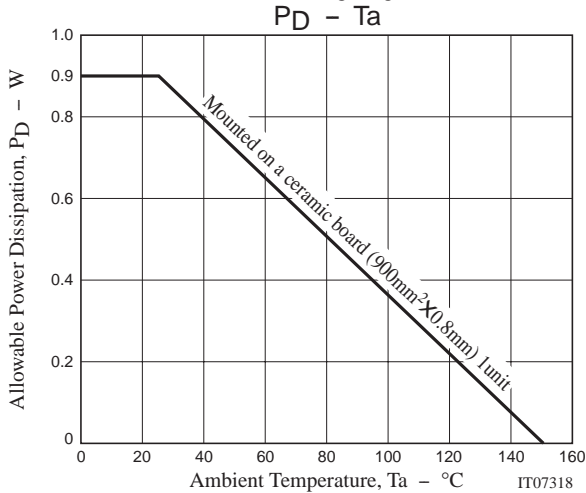
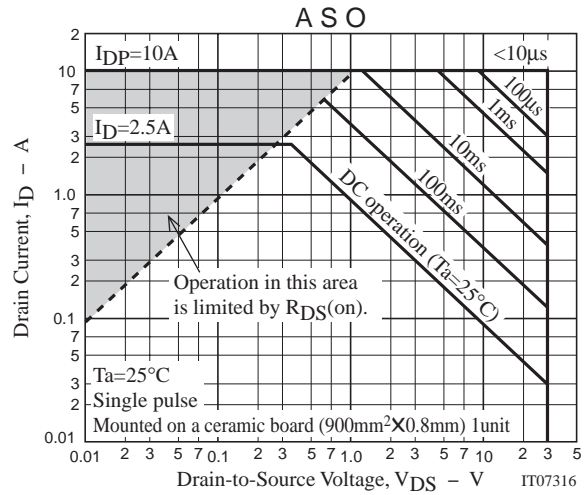
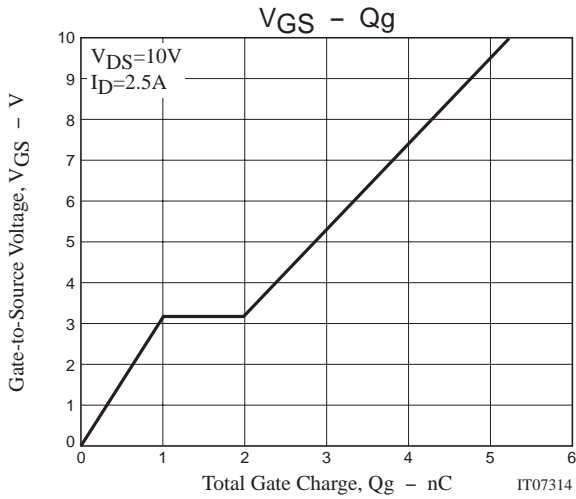
- 1 : Gate1
- 2 : Source2
- 3 : Gate2
- 4 : Drain2
- 5 : Source1
- 6 : Drain1

Top view

Switching Time Test Circuit







Note on usage : Since the CPH6616 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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